



ZXTN619MA

50V NPN LOW SATURATION TRANSISTOR

Features

- $BV_{CEO} > 50V$
- I_C = 4A Continuous Collector Current
- Low Saturation Voltage (100mV Max @1A)
- $R_{SAT} = 68m\Omega$ for a Low Equivalent On-Resistance
- hFE Specified up to 6A for High Current Gain Hold Up
- Low Profile 0.6mm High Package for Thin Applications
- R_{0JA} Efficient, 60% Lower than SOT23
- 4mm² Footprint, 50% Smaller than SOT23
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (ZXTN619MAQ)

U-DFN2020-3 (Type B)

Mechanical Data

- Case: U-DFN2020-3
- Nominal Package Height: 0.6mm
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu, Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.01 grams (Approximate)

Applications

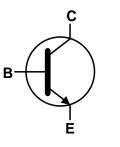
- MOSFET Gate Driving
- **DC-DC Converters** •
- **Charging Circuits**
- Motor Control
- **Power Switches**

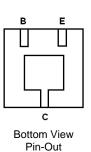


Top View



Bottom View





Device Symbol

Ordering Information (Note 4)

	Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
	ZXTN619MATA	SC	7	8	3,000
Notes:	1. No purposely added lea	d. Fully EU Directive 2002/95/	EC (RoHS), 2011/65/EU (RoHS :	2) & 2015/863/EU (RoHS 3) comp	liant.

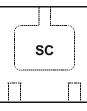
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



SC = Product Type Marking code

Top View



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Parameter		Symbol	Limit	Unit		
Collector-Base Voltage		V _{CBO}	100			
Collector-Emitter Voltage		V _{CEO}	50	V		
Emitter-Base Voltage		V _{EBO}	7			
Peak Pulse Current		ICM	6			
Continuous Collector Current (Note 5) (Note 6)			4			
		IC	4.3	A		
Base Current		IB	1			

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)		1.5 12	W	
Linear Derating Factor	(Note 6)	– P _D	2.45 19.6	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 5)	Р	83		
Thermal Resistance, Junction to Amblent	(Note 6)	R _{θJA}	51	°C/W	
Thermal Resistance, Junction to Lead (Note 7)		R _θ JL	16.8		
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

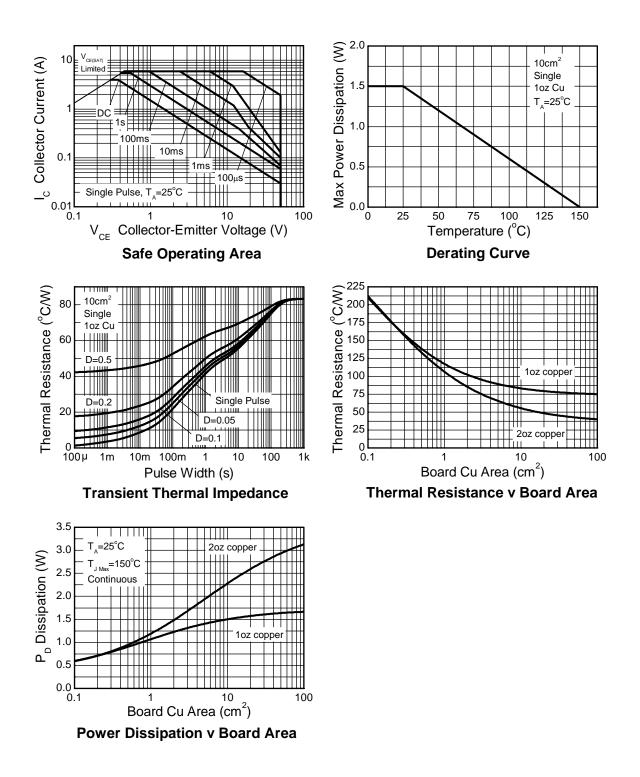
ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

5. For a device mounted with the exposed collector pad on 31mm x 31mm (10cm²) 1oz copper that is on a single sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state. The entire exposed collector pad is attached to the heatsink.
6. Same as Note 5, except the device is measured at t ≤ 5s.
7. Thermal resistance from junction to solder-point (on the exposed collector pad).
8. Refer to JEDEC specification JESD22-A114 and JESD22-A115. Notes:



Thermal Characteristics and Derating Information





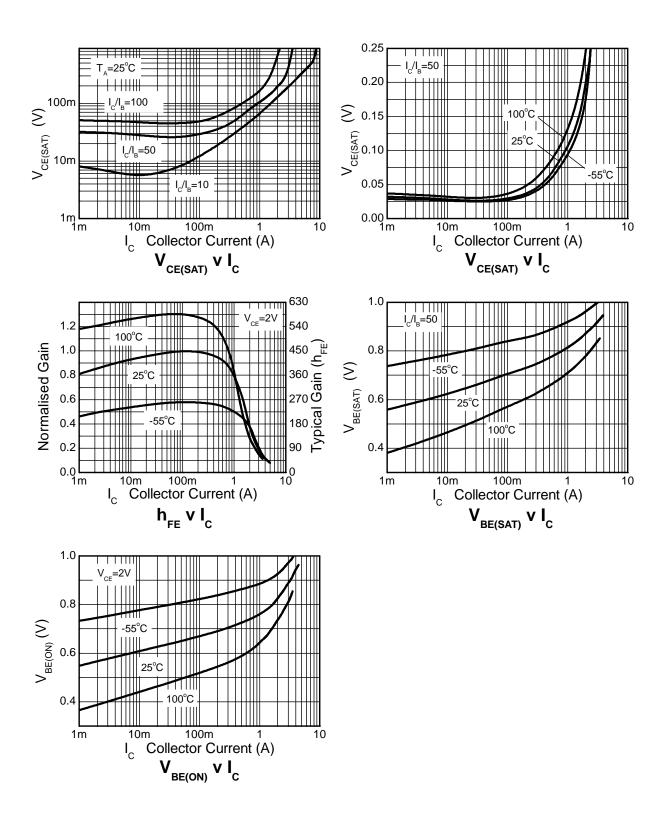
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	100	190	_	V	I _C = 100μA
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	50	65	_	V	$I_{C} = 10 \text{mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	7	8.2	_	V	I _E = 100μA
Collector Cutoff Current	I _{CBO}	—	-	100	nA	V _{CB} = 80V
Emitter Cutoff Current	I _{EBO}	—		20	nA	$V_{EB} = 6V$
Collector Emitter Cutoff Current	ICES	—	-	100	nA	$V_{CES} = 40V$
Static Forward Current Transfer Ratio (Note 9)	hfe	200 300 200 100 —	400 450 400 225 40		—	$\begin{split} I_{C} &= 10 \text{mA}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 200 \text{mA}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 1 \text{A}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 2 \text{A}, \ V_{CE} = 2 \text{V} \\ I_{C} &= 6 \text{A}, \ V_{CE} = 2 \text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 9)	$V_{\text{CE}(\text{SAT})}$	- - - -	10 70 145 150 225 270	20 100 200 220 300 320	mV	$\begin{split} I_{C} &= 0.1A, \ I_{B} = 10 mA \\ I_{C} &= 1A, \ I_{B} = 50 mA \\ I_{C} &= 1A, \ I_{B} = 10 mA \\ I_{C} &= 2A, \ I_{B} = 50 mA \\ I_{C} &= 3A, \ I_{B} = 100 mA \\ I_{C} &= 4A, \ I_{B} = 200 mA \end{split}$
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(ON)}	—	0.94	1.00	V	$I_{C} = 4A, V_{CE} = 2V$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(SAT)}	—	1.00	1.07	V	$I_{C} = 4A, I_{B} = 200 \text{mA}$
Output Capacitance	C _{OBO}	—	12	20	pF	$V_{CB} = 10V$, f = 1MHz
Transition Frequency	f _T	100	165	_	MHz	$V_{CE} = 10V, I_C = 50mA,$ f = 100MHz
Turn-On Time	t _{ON}	—	170		ns	$V_{CC} = 10V, I_C = 1A$
Turn-Off Time	t _{OFF}	—	750	_	ns	$I_{B1} = -I_{B2} = 10 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



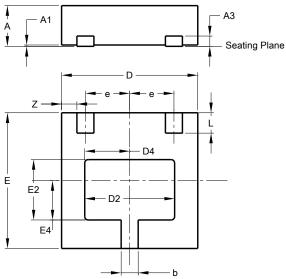
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

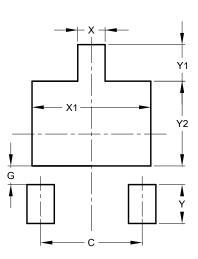
Please see http://www.diodes.com/package-outlines.html for the latest version.



	U-DFN2020-3 (Type B)							
Dim	Min	Max	Тур					
Α	0.57	0.63	0.60					
A1	0.00	0.05	0.02					
A3			0.152					
b	0.20	0.30	0.25					
D	1.950	2.075	2.00					
D2	1.22	1.42	1.32					
D4	0.56	0.76	0.66					
E	1.950	2.075	2.00					
E2	0.79	0.99	0.89					
E4	0.48	0.68	0.58					
е			0.65					
L	0.25	0.35	0.30					
Z	_		0.225					
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



U-DFN2020-3 (Type B)

Dimensions	Value (in mm)		
С	1.300		
G	0.240		
Х	0.350		
X1	1.520		
Y	0.500		
Y1	0.470		
Y2	1.090		



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